# SK 120 KQ



### Antiparallel Thyristor Module

#### SK 120 KQ

Preliminary Data

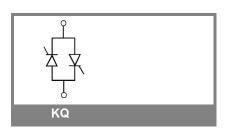
### Features

- Compact Design
- One screw mounting
- Heat transfer and isolation through direct copper bonded aluminium oxide ceramic (DBC)
- Glass passived thyristor chips
- Up to 1600V reverse voltage
- UL recognized, file no. E 63 532

### **Typical Applications\***

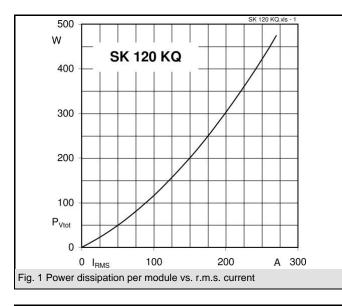
- Soft starters
- Light control (studios, theaters...)
- Temperature control

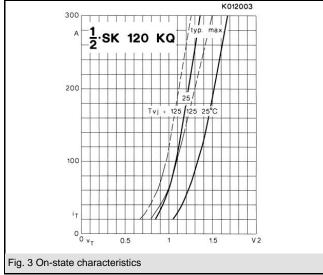
V		V <sub>RRM</sub> , V <sub>DRM</sub>		I <sub>RMS</sub> = 134 A (full conduction)	
V <sub>RSM</sub> V		V RRM <sup>,</sup> V DRM			
900		v 800		(T <sub>s</sub> = 85 °C) SK 120 KQ 08	
1300		1200		SK 120 KQ 08	
1700		1600		SK 120 KQ 16	
1700		1600		SK 120 KQ 16	
Symbol	Con	ditions		Values	Units
I <sub>RMS</sub>		W1C ; sin. 180° ; T <sub>s</sub> = 100°C		94	A
RMS	W1C ; sin. 180° ; $T_s = 85^{\circ}C$		134	A	
1	$T_{vi} = 25 \text{ °C}; 10 \text{ ms}$		2000	A	
I <sub>TSM</sub>		125 °C ; 10 ms		1800	A
i²t	$T_{vi} = 25 \text{ °C}; 8,310 \text{ ms}$			20000	A²s
	v <sub>j</sub> T <sub>vi</sub> = 125 °C ; 8,310 ms			16200	A²s
V <sub>T</sub>	$T_{vi} = 25 \text{ °C, } I_T = 300 \text{ A}$			max. 1,85	V
V <sub>T(TO)</sub>	$T_{vi} = 125 \text{ °C}$			max. 0,9	v
r <sub>T</sub>	$T_{vi} = 125 \text{ °C}$			max. 3,5	mΩ
I <sub>DD</sub> ;I <sub>RD</sub>		25 °C, V <sub>RD</sub> =V <sub>RRM</sub>		max. 1	mA
		125 °C, V <sub>RD</sub> =V <sub>RRM</sub>		max. 20	mA
t <sub>gd</sub>		T <sub>vi</sub> = 25 °C, I <sub>G</sub> = 1 A; di <sub>G</sub> /dt= 1 A/μs		1	μs
t <sub>gr</sub>	$V_{\rm D} = 0.67 \ {}^{*}V_{\rm DRM}$			2	μs
(dv/dt) <sub>cr</sub>	T <sub>vi</sub> = 125 °C			1000	V/µs
(di/dt) <sub>cr</sub>	T <sub>vi</sub> = 125 °C; f= 5060 Hz			100	A/µs
t <sub>q</sub>		125 °C; typ.		80	μs
I <sub>H</sub>	T <sub>vj</sub> = 25 °C; typ. / max.			100 / 200	mA
ΙL	$T_{vj}$ = 25 °C; $R_G$ = 33 $\Omega$ ; typ. / max.			200 / 500	mA
V <sub>GT</sub>	T <sub>vj</sub> = 25 °C; d.c.			min. 2	V
I <sub>GT</sub>	T <sub>vj</sub> = 25 °C; d.c.			min. 100	mA
V <sub>GD</sub>	T <sub>vj</sub> = 125 °C; d.c.			max. 0,25	V
I <sub>GD</sub>	T <sub>vj</sub> =	T <sub>vj</sub> = 125 °C; d.c.		max. 5	mA
R <sub>th(j-s)</sub>	cont.	per thyristor		0,45	K/W
		80° per thyristor		0,47	K/W
R <sub>th(j-s)</sub>		per W1C		0,225	K/W
	sin 1	80° per W1C		0,235	K/W
T <sub>vj</sub>				-40 +125	℃ ℃
T <sub>stg</sub>				-40 +125	-
T <sub>solder</sub>	terminals, 10s		260	°C	
V <sub>isol</sub>	a. c. 50 Hz; r.m.s.; 1 s / 1 min.		3000 / 2500	V~	
M <sub>s</sub>	Mour	nting torque to heatsin	IK	2,0	Nm
M <sub>t</sub>					Nm m/c²
a				10	m/s²
m				19	g
Case	SEMITOP <sup>®</sup> 2			Τ2	

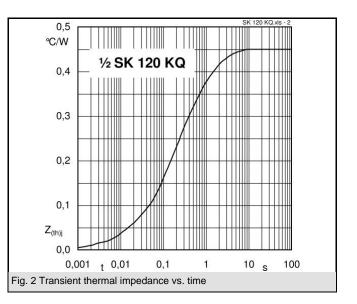


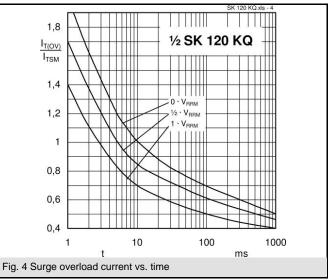
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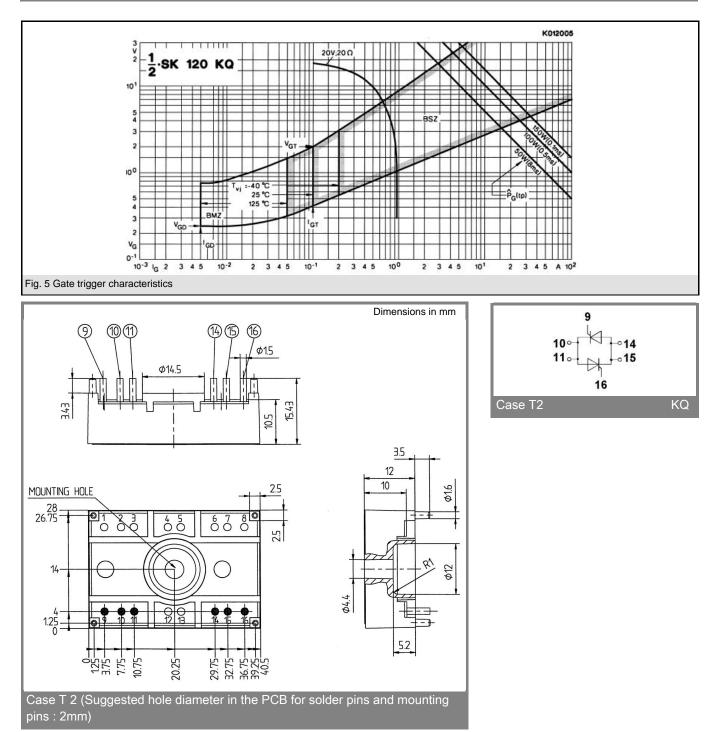








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\* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our personal.